



DEPOSITION SYSTEMS FOR COMPOUND SEMICONDUCTORS

AIX G5 HT-TM Planetary Reactor®

AIXTRON
Our technology. Your future.

Single wafer performance with batch reactor benefits

AIX G5 HT-TM

Increase your productivity and performance

- ▶ Chosen by the best in the industry
- ▶ Available configurations: 56 x 2 inch, 14 x 4 inch, 8 x 6 inch
- ▶ Highest throughput with transfer module
- ▶ Lowest Cost of Ownership
- ▶ Highest yield performance with
 - Cl₂ in-situ cleaning
 - Auto feed forward for wafer level temperature correction

AIX G5 HT-TM characteristics

- ▶ Unique axis symmetric wafer performance like Si single wafer reactor
 - Wafer bow
 - Thickness, composition, concentration
 - Device yield
- ▶ Warm ceiling results in lowest heat flux through wafer
 - Smallest wafer bow by vertical temperature gradient
 - Enabling standard Si wafer thickness
- ▶ Customized temperature optimization by recess shaping

Process and Transfer Module



Single Wafer Performance with Batch Reactor Cost Benefit

Thickness uniformity 1.07 % standard deviation without edge exclusion. Mean thickness 3.58 µm.

